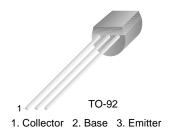


June 2007

BC183

NPN General Purpose Amplifer



Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|------------|-------|
| V _{CBO} | Collector-Base Voltage | 45 | V |
| V_{CEO} | Collector-Emitter Voltage | 30 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| I _C | Collector Current (DC) | 100 | mA |
| P _C | Collector Dissipation (T _a =25°C) | 350 | mW |
| T _{STG} , T _J | Storage Junction Temperature Range | - 55 ~ 150 | °C |

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Conditions | Min. | Max | Units |
|-----------------------|--------------------------------------|---|----------|-------------|-------|
| BV _{CBO} | Collector-Base Voltage | $I_C = 10\mu A$ | 45 | | V |
| BV _{CEO} | Collector-Emitter Voltage | I _C = 2mA | 30 | | V |
| BV _{EBO} | Emitter-Base Voltage | $I_E = 10\mu A$ | 5 | | V |
| I _{CBO} | Collector Cut-off Current | V _{CB} = 30V | | 15 | nA |
| I _{EBO} | Emitter Cut-off Current | V _{EB} = 4.0V | | 15 | nA |
| h _{FE} | DC Current Gain | $V_{CE} = 5V, I_{C} = 10\mu A$ $V_{CE} = 5V, I_{C} = 100m A$ | 40 80 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$ $I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$ | | 0.25 0.6 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_{C} = 100 \text{mA}, I_{B} = 5 \text{mA}$ | | 1.2 | V |
| V _{BE} (on) | Base-Emitter On Voltage | $V_{CE} = 5V$, $I_C = 2mA$ | 0.55 | 0.7 | V |
| C _{OB} | Output Capacitance | V _{CE} = 10V, f = 1.0MHz | | 5 | pF |
| f _T | Current gain Bandwidth Product | $V_{CE} = 5V, I_{C} = 10mA,$ f = 100MHz | 150 | | MHz |
| h _{fe} | Small Signal Current Gain | V _{CE} = 5V, I _C = 2mA 125 900 f = 1KHz | | 900 | |
| NF | Noise Figure | $V_{CE} = 5V$, $I_{C} = 200$ mA $R_{G} = 2$ K Ω , $f = 1$ KHz | | 10 | dB |

Typical Characteristics

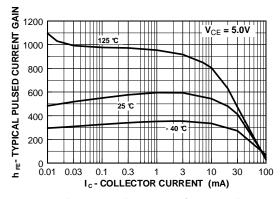
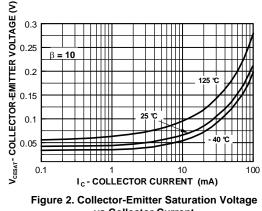


Figure 1. Typical Pulsed Current Gain vs Collector Current



vs Collector Current

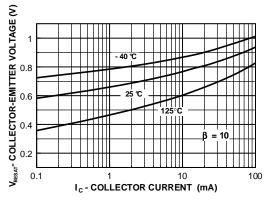


Figure 3. Base-Emitter Saturation Voltage vs Collector Curent

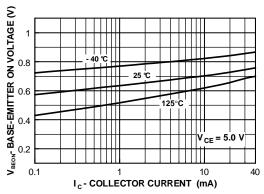


Figure 4. Base-Emitter ON Voltage vs Collector Current

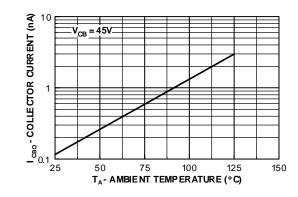


Figure 5. Collector-Cutoff Current vs Ambient Temperature

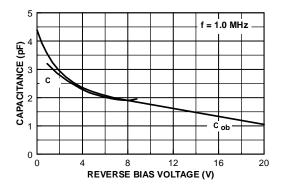


Figure 6. Input and Output Capacitance vs Reverse Bias Voltage





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